

TOSHIBA TRANSISTOR SILICON PNP TRIPLE DIFFUSED TYPE (PCT PROCESS)

2SA1200

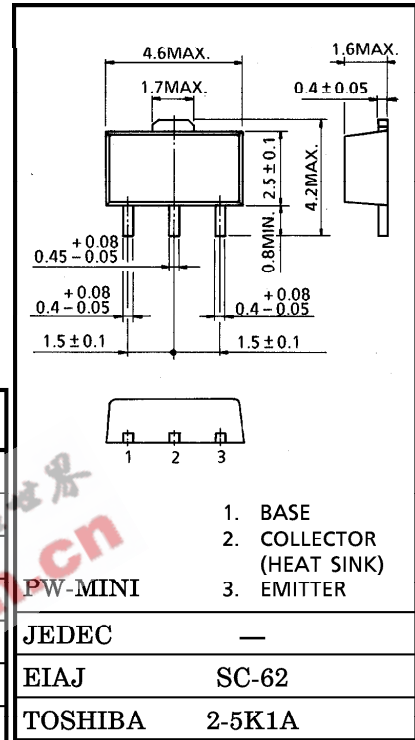
HIGH VOLTAGE SWITCHING APPLICATIONS

Unit in mm

- High Voltage : $V_{CEO} = -150V$
- High Transition Frequency : $f_T = 120MHz$ (Typ.)
- $P_C = 1 \sim 2W$ (Mounted on Ceramic Substrate)
- Small Flat Package
- Complementary to 2SC2880

MAXIMUM RATINGS ($T_a = 25^\circ C$)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	-150	V
Collector-Emitter Voltage	V_{CEO}	-150	V
Emitter-Base Voltage	V_{EBO}	-5	V
Collector Current	I_C	-50	mA
Base Current	I_B	-10	mA
Collector Power Dissipation	P_C	500	mW
Collector Power Dissipation	P_C^*	800	mW
Junction Temperature	T_j	150	$^\circ C$
Storage Temperature Range	T_{stg}	-55~150	$^\circ C$



Weight : 0.05g

Marking

P_C^* : 2SA1200 mounted on ceramic substrate ($250mm^2 \times 0.8t$)

Type Name

hFE Rank



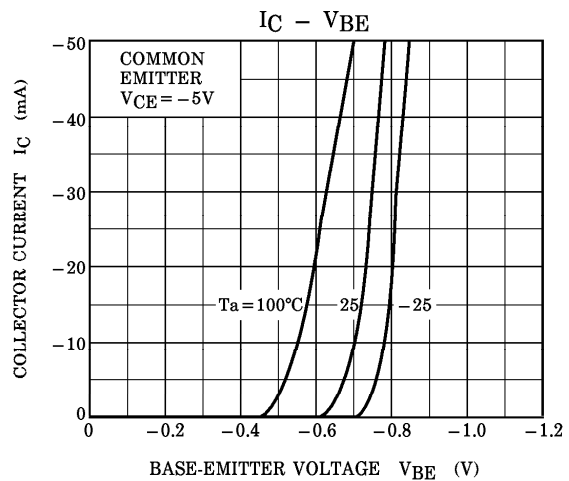
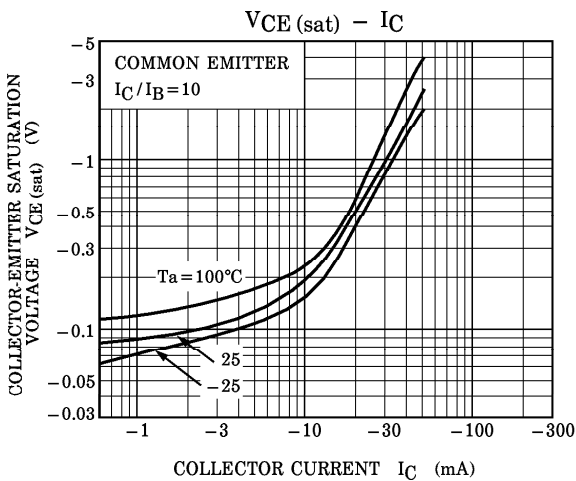
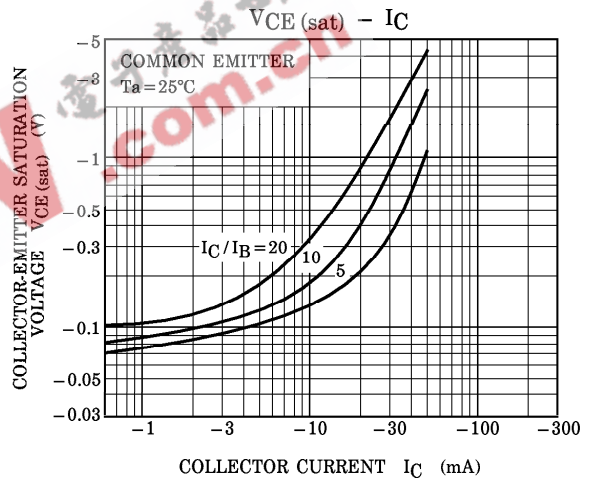
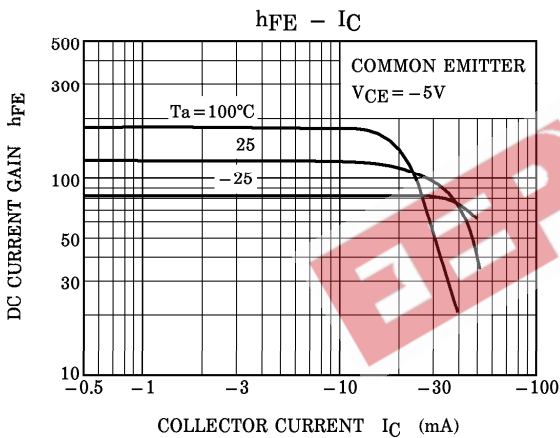
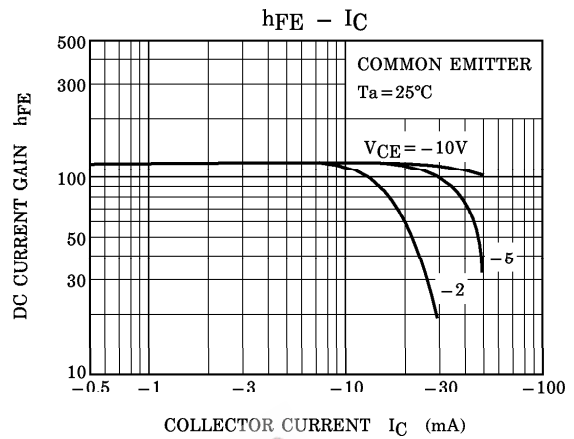
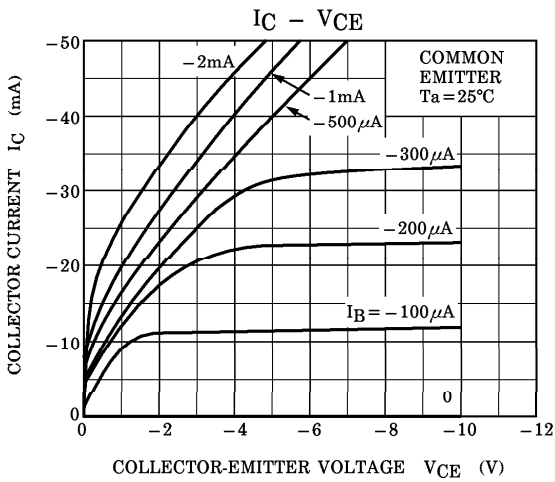
ELECTRICAL CHARACTERISTICS ($T_a = 25^\circ C$)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I_{CBO}	$V_{CB} = -150V, I_E = 0$	—	—	-0.1	μA
Emitter Cut-off Current	I_{EBO}	$V_{EB} = -5V, I_C = 0$	—	—	-0.1	μA
DC Current Gain	h_{FE} (Note)	$V_{CE} = -5V, I_C = -10mA$	70	—	240	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = -10mA, I_B = -1mA$	—	—	-0.8	V
Base-Emitter Voltage	V_{BE}	$V_{CE} = -5V, I_C = -30mA$	—	—	-0.9	V
Transition Frequency	f_T	$V_{CE} = -30V, I_C = -10mA$	—	120	—	MHz
Collector Output Capacitance	C_{ob}	$V_{CE} = -10V, I_E = 0, f = 1MHz$	—	4.0	5.0	pF

Note : hFE Classification O : 70~140, Y : 120~240

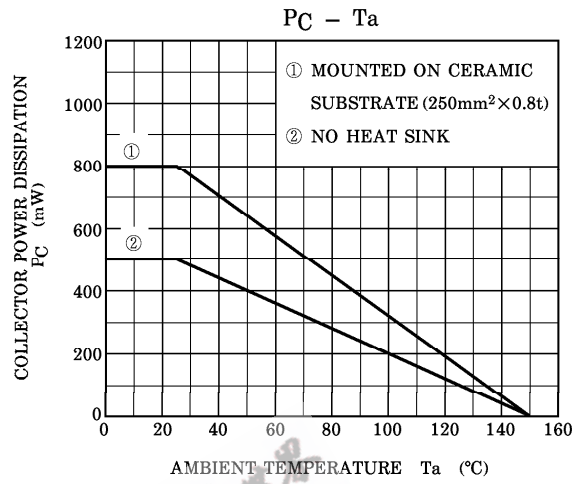
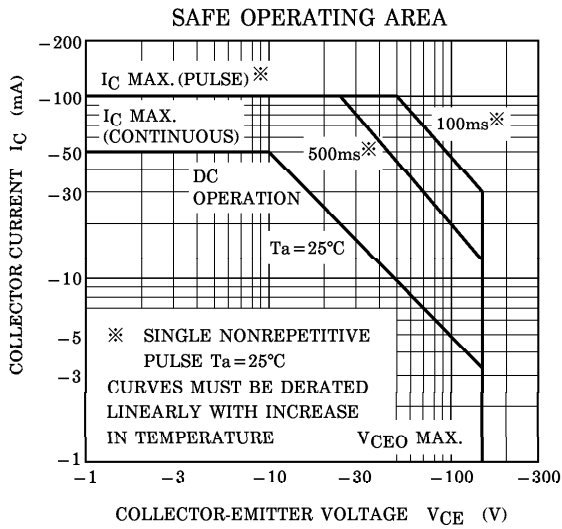
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